



PE2319T P-Channel Enhancement Mode Power MOSFET

PE2319T Description

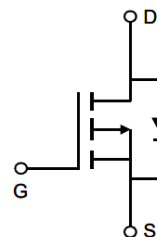
The PE2319T uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. It can be used in a wide variety of applications.

PE2319T General Features

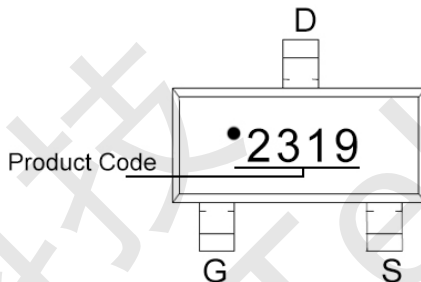
- $V_{DS} = -20V$, $I_D = -8A$
- $R_{DS(ON)} < 23m\Omega$ @ $V_{GS} = -4.5V$
- $R_{DS(ON)} < 31m\Omega$ @ $V_{GS} = -2.5V$
- High Power and current handing capability
- Lead free product is acquired
- Surface Mount Package

PE2319T Application

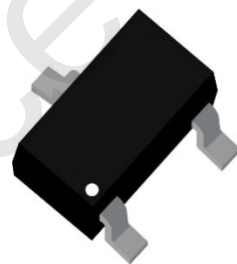
- PWM applications
- Load switch
- Power management



Schematic diagram



Marking and pin assignment



SOT-23-3L

PE2319T Absolute Maximum Ratings ($T_A = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	± 12	V
Drain Current-Continuous	I_D	-8	A
Pulsed Drain Current (Note 1)	I_{DM}	-24	A
Maximum Power Dissipation	P_D	1.5	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ C$

PE2319T Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	83	$^\circ C/W$
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PE2319T Electrical Characteristics (TA=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=-250\mu A$	-20	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-18V, V_{GS}=0V$	-	-	-1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 12V, V_{DS}=0V$	-	-	± 100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-0.45	-0.7	-1.2	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=-4.5V, I_D=-5A$	-	19	23	m Ω
		$V_{GS}=-2.5V, I_D=-3A$	-	25	31	m Ω
Dynamic Characteristics (Note 4)						
Input Capacitance	C_{iss}	$V_{DS}=-10V, V_{GS}=0V,$ $F=1.0MHz$	-	1290	-	pF
Output Capacitance	C_{oss}		-	240	-	pF
Reverse Transfer Capacitance (Note 4)	C_{rss}		-	200	-	pF
Switching Characteristics						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=-10V, I_D=-1A, R_L=1\Omega,$ $V_{GS}=-4.5V, R_G=3\Omega$	-	15	-	nS
Turn-on Rise Time	t_r		-	98.4	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	42.4	-	nS
Turn-Off Fall Time	t_f		-	19.6	-	nS
Total Gate Charge	Q_g	$V_{DS}=-10V, I_D=-5A,$ $V_{GS}=-4.5V$	-	21	-	nC
Gate-Source Charge	Q_{gs}		-	2.3	-	nC
Gate-Drain Charge	Q_{gd}		-	2.4	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	$V_{GS}=0V, I_S=-1A$	-	-	-1.2	V
Diode Forward Current (Note 2)	I_S		-	-	-8	A
Reverse Recovery Time	t_{rr}	$I_F=-5A, di/dt=100A/\mu s$	-	30	-	nS
Reverse Recovery Charge	Q_{rr}		-	11	-	nC

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to product.



PE2319T Typical Electrical and Thermal Characteristics

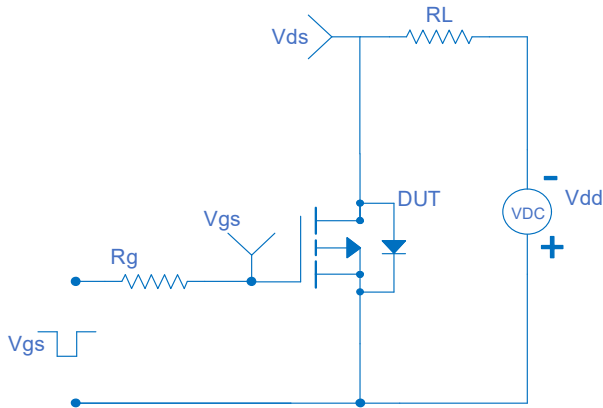


Figure 1 Switching Test Circuit

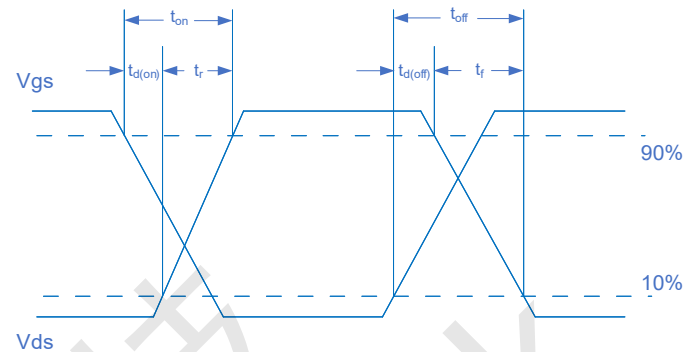


Figure 2 Switching Waveform

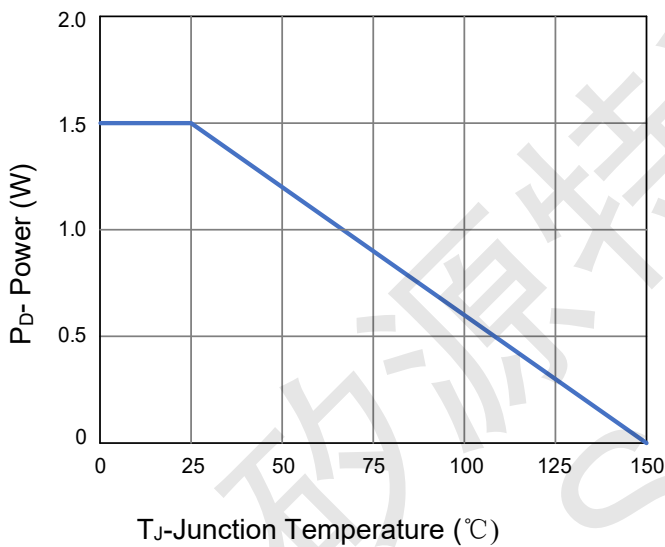


Figure 3 Power De-rating

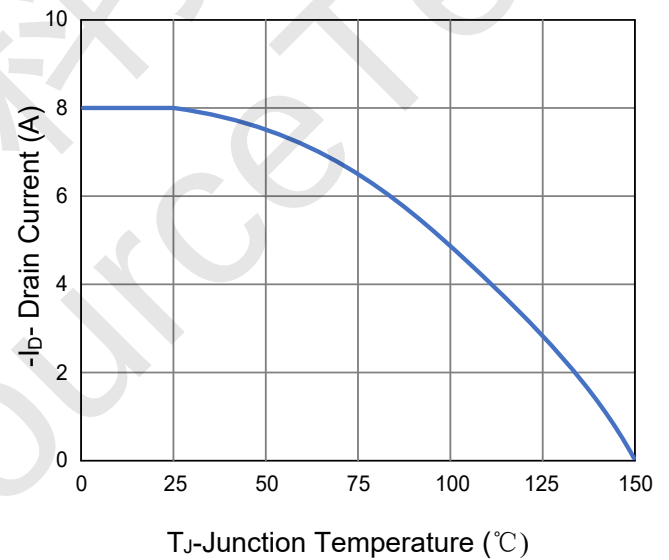


Figure 4 Drain Current

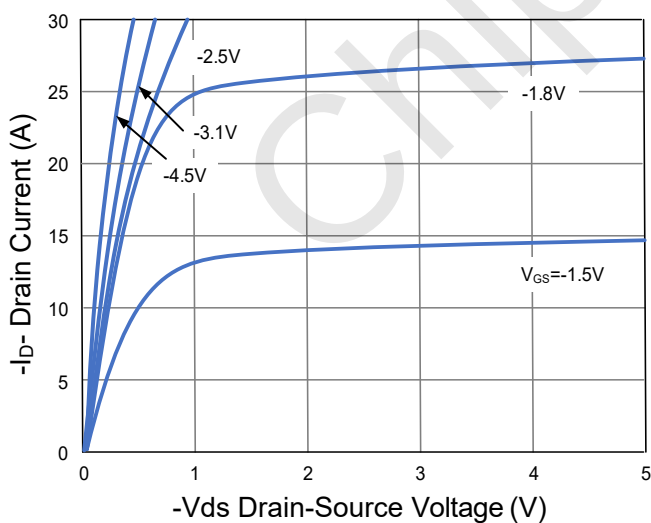


Figure 5 Output Characteristics

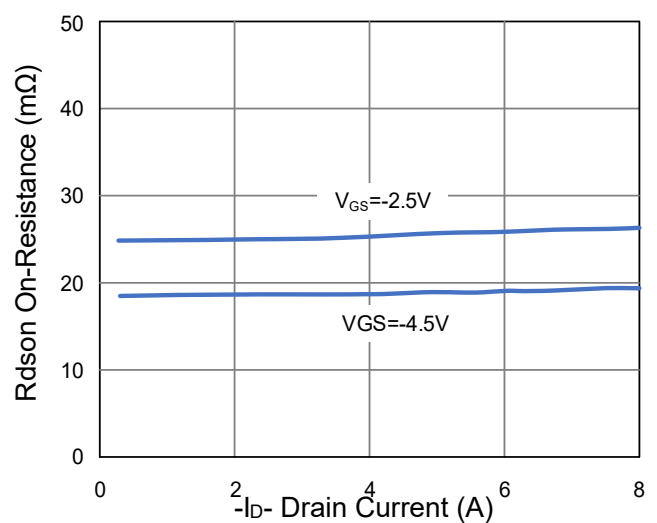


Figure 6 Rdson vs Drain Current

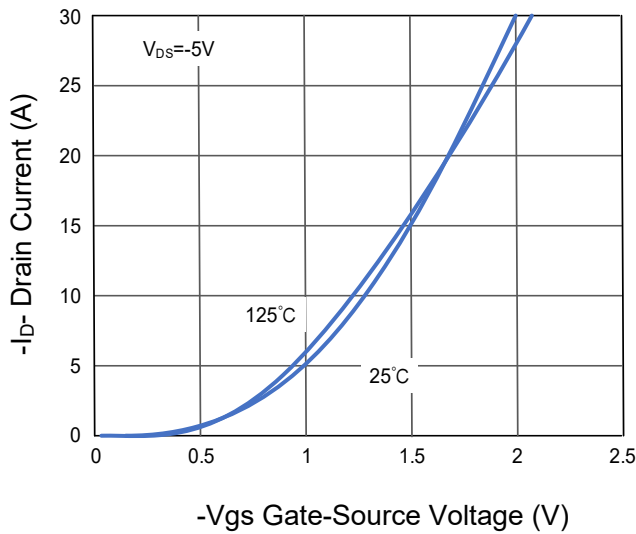


Figure 7 Transfer Characteristics

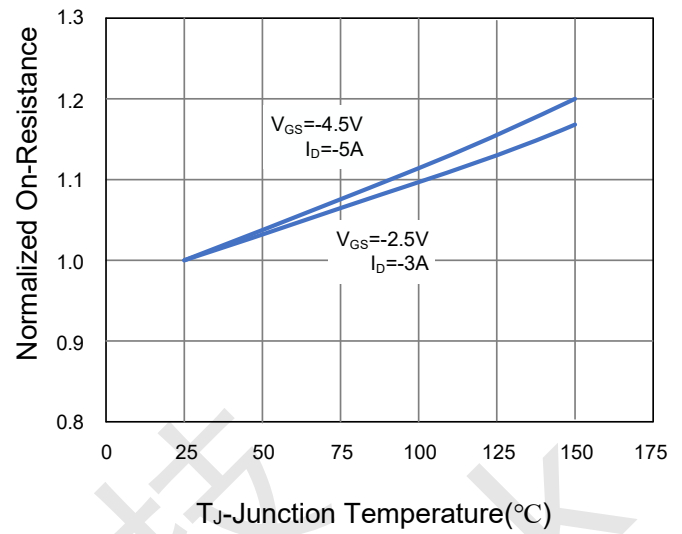


Figure 8 $R_{DS(on)}$ vs Junction Temperature

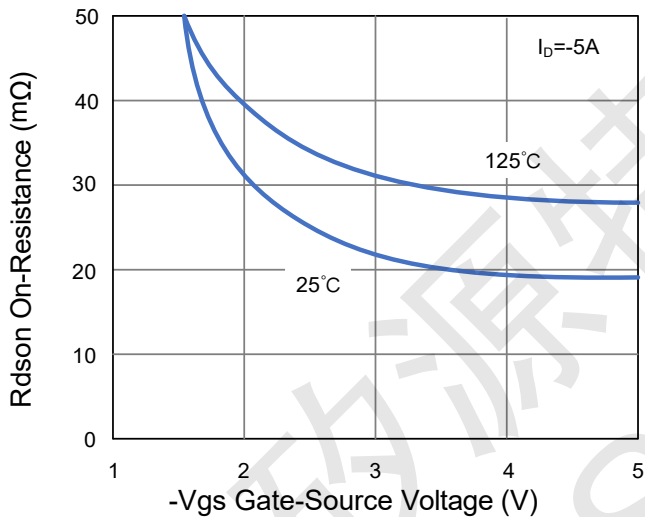


Figure 9 $R_{DS(on)}$ vs V_{GS}

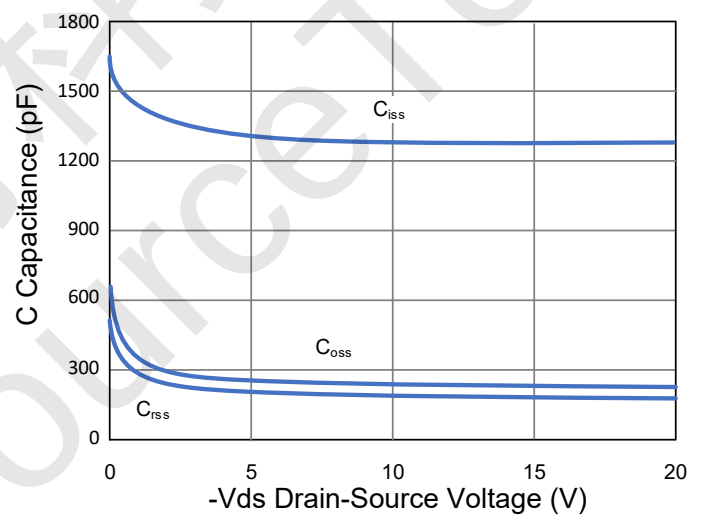


Figure 10 Capacitance vs V_{DS}

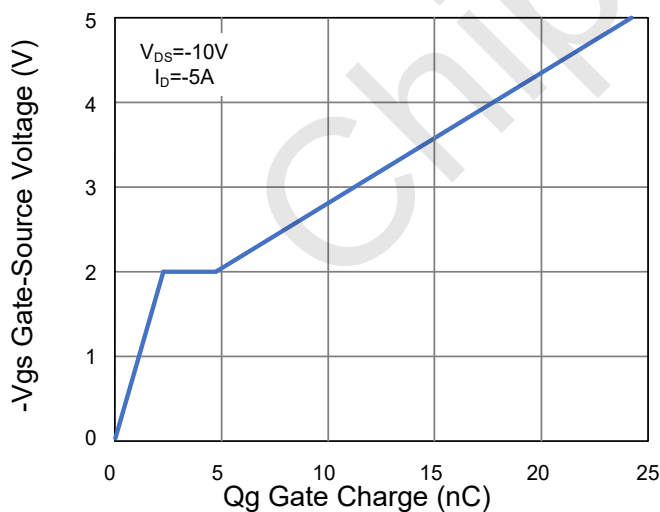


Figure 11 Gate Charge

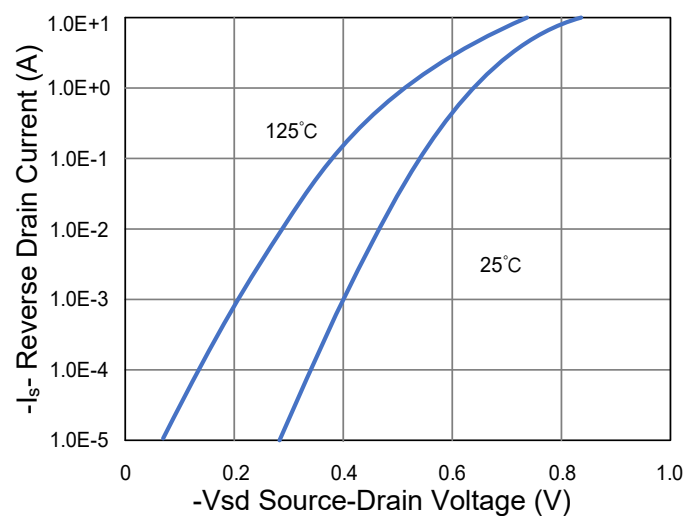


Figure 12 Source- Drain Diode Forward

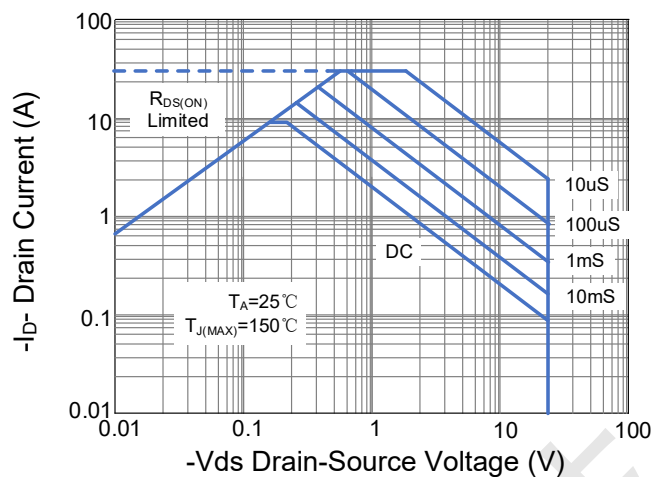


Figure 13 Safe Operation Area

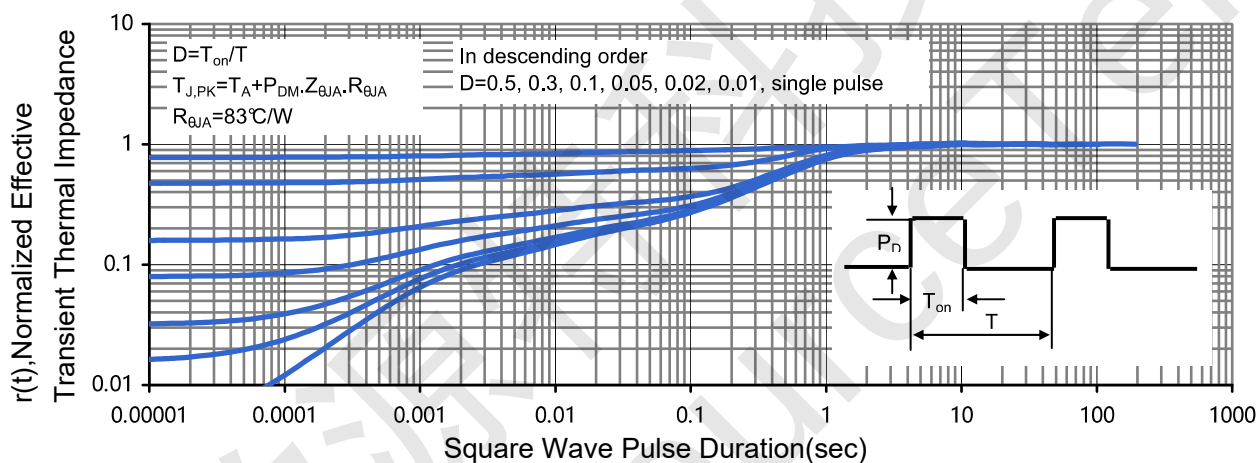
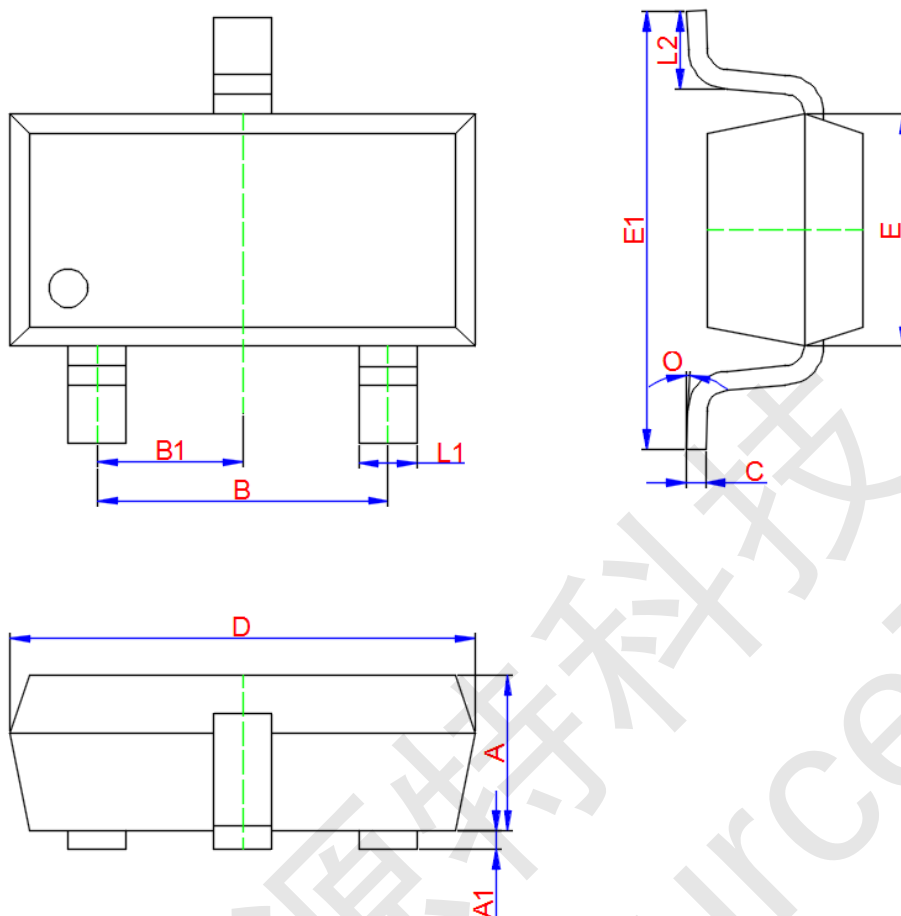


Figure 14 Normalized Maximum Transient Thermal Impedance



PE2319T SOT-23-3L Package Information



Symbol	Dimensions In Millimeters		
	Min.	Typ.	Max.
A	1.050	1.100	1.150
A1	0.000	0.050	0.100
L1	0.300	0.400	0.500
C	0.100	0.150	0.200
D	2.820	2.920	3.020
E	1.500	1.600	1.700
E1	2.650	2.800	2.950
B	1.800	1.900	2.000
B1	0.950 TYP.		
L2	0.300	0.450	0.600
O	0°	4°	8°